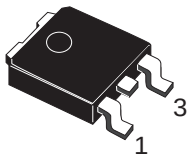
STD40NF3LL

N-CHANNEL 30V - 0.009 Ω - 40A DPAK
LOW GATE CHARGE STripFET™II POWER MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STD40NF3LL	30 V	<0.011 Ω	40 A

- TYPICAL R_{DS}(on) = 0.009 Ω @ 10V
- OPTIMAL $R_{DS(on)}$ x Qg TRADE-OFF
- CONDUCTION LOSSES REDUCED
- SWITCHING LOSSES REDUCED)
- SURFACE-MOUNTING DPAK (TO-252) POWER PACKAGE IN TAPE & REEL (SUFFIX “T4")



DPAK
TO-252
(Suffix “T4”)

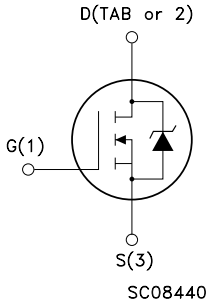
DESCRIPTION

This application specific Power MOSFET is the third genaration of STMicroelectronis unique "Single Feature Size™" strip-based process. The resulting transistor shows the best trade-off between on-resistance and gate charge. When used as high and low side in buck regulators, it gives the best performance in terms of both conduction and switching losses. This is extremely important for motherboards where fast switching and high efficiency are of paramount importance.

APPLICATIONS

- SPECIFICALLY DESIGNED AND OPTIMISED FOR HIGH EFFICIENCY CPU CORE DC/DC CONVERTERS
- AUTOMOTIVE SWITCHING APPLICATIONS

INTERNAL SCHEMATIC DIAGRAM



Ordering Information

SALES TYPE	MARKING	PACKAGE	PACKAGING
STD40NF3LLT4	D40NF3LL@	TO-252	TAPE & REEL

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	30	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	30	V
V_{GS}	Gate- source Voltage	± 16	V
I_D(•)	Drain Current (continuous) at T_C = 25°C	40	A
I_D	Drain Current (continuous) at T_C = 100°C	28	A
I_{DM}(••)	Drain Current (pulsed)	160	A
P_{tot}	Total Dissipation at T_C = 25°C	80	W
	Derating Factor	0.53	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	5.5	V/ns
E_{AS} (2)	Single Pulse Avalanche Energy	850	mJ
T_{stg}	Storage Temperature	-55 to 175	°C
T_j	Operating Junction Temperature		

(•) Current limited by the package
(••) Pulse width limited by safe operating area.

(1) I_{SD} ≤40A, di/dt ≤350A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_j ≤ T_{JMAX}
(2) Starting T_j = 25 °C, I_D = 20A, V_{DD} = 25V

NEW DATASHEET ACCORDING TO PCN DSG/CT/2C13 MARKING:D40NF3LL @

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	1.88	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	100	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	Typ	300	°C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	30			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating T_C = 125°C			1 10	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 16 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250 µA	1			V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V I_D = 20 A V_{GS} = 4.5 V I_D = 10 A		0.0090 0.0115	0.0110 0.0135	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	V_{DS} = 15 V I_D = 20 A		23		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		1650 540 130		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	V_{DD} = 15 V I_D = 20 A R_G = 4.7 Ω V_{GS} = 4.5 V (Resistive Load, Figure 3)		23 156		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD}=15 V I_D =40 A V_{GS} =4.5 V		24 8.5 12	33	nC nC nC

SWITCHING OFF

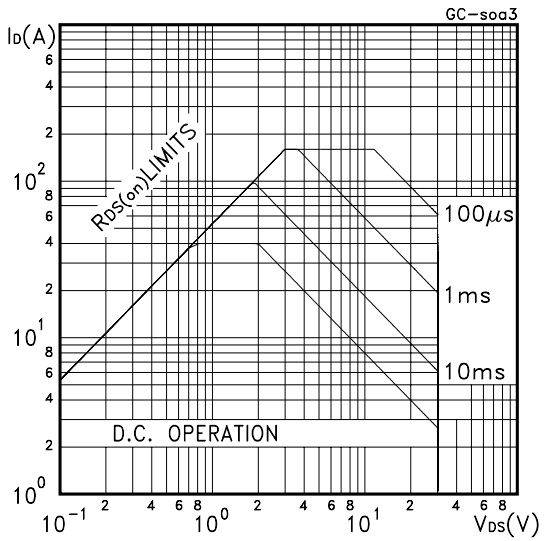
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	V_{DD} = 15 V I_D = 20 A R_G = 4.7Ω, V_{GS} = 4.5 V (Resistive Load, Figure 3)		27 28		ns ns

SOURCE DRAIN DIODE

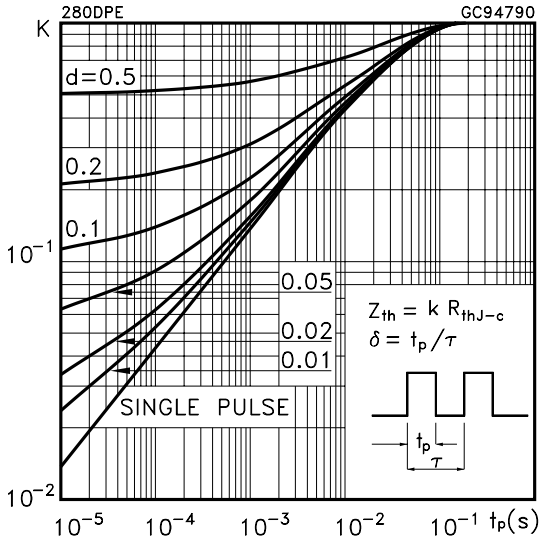
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (•)	Source-drain Current Source-drain Current (pulsed)				40 160	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 40 A V_{GS} = 0			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 40 A di/dt = 100A/µs V_{DD} = 15 V T_j = 150°C (see test circuit, Figure 5)		40 50 2.5		ns nC A

(*)Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
(•)Pulse width limited by safe operating area.

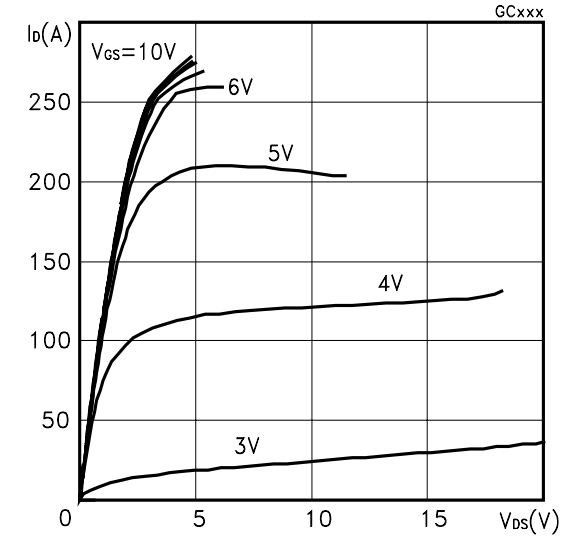
Safe Operating Area



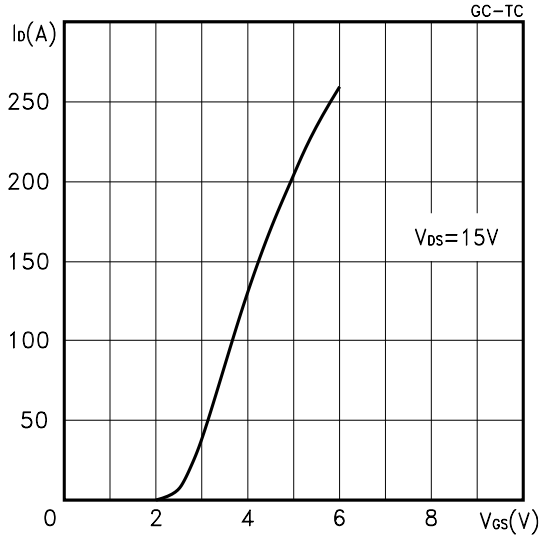
Thermal Impedance



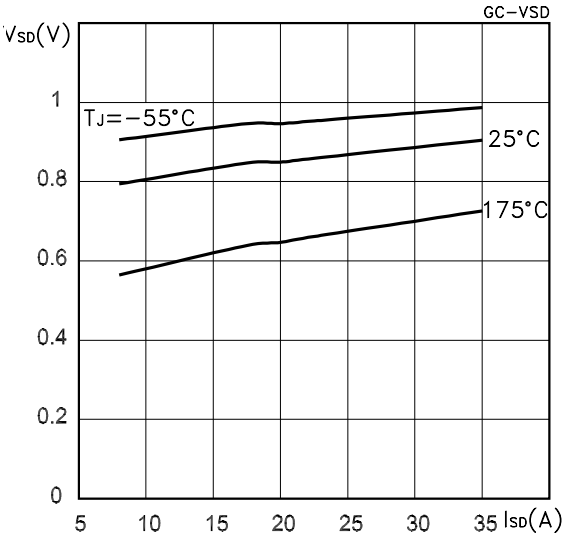
Output Characteristics



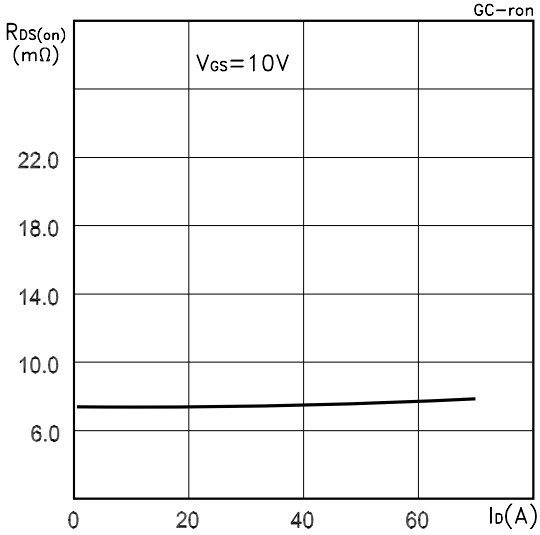
Transfer Characteristics



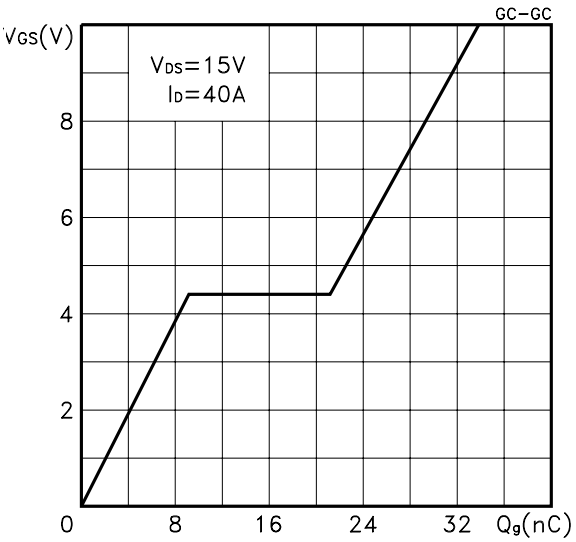
Source-drain Diode Forward Characteristics



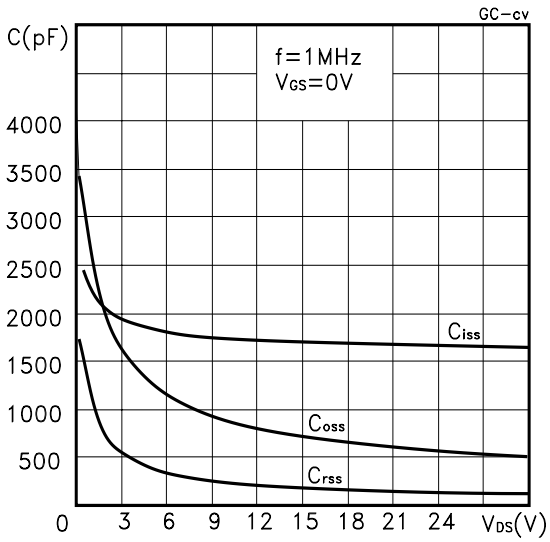
Static Drain-source On Resistance



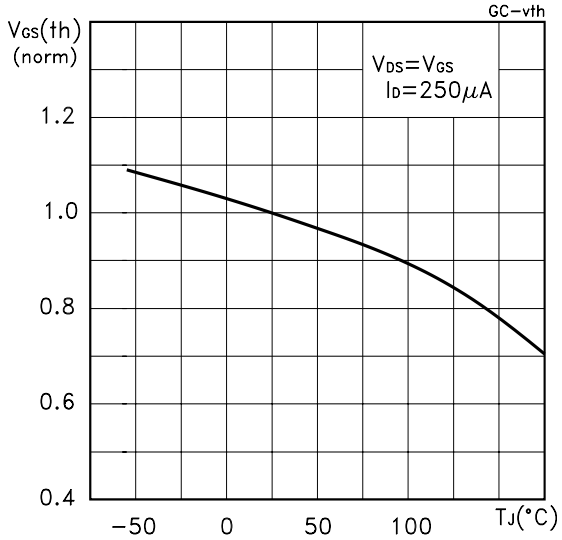
Gate Charge vs Gate-source Voltage



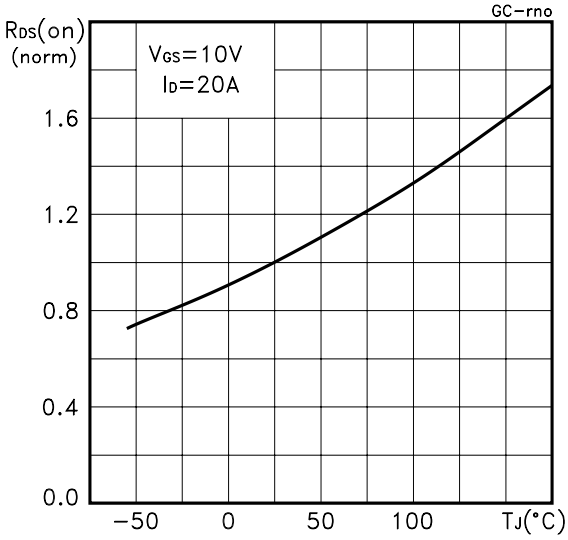
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Normalized Breakdown Voltage vs Temperature.

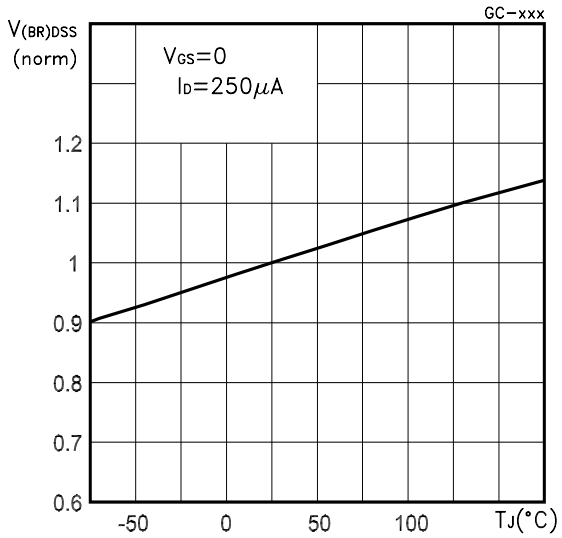


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Fig. 1: Unclamped Inductive Load Test Circuit

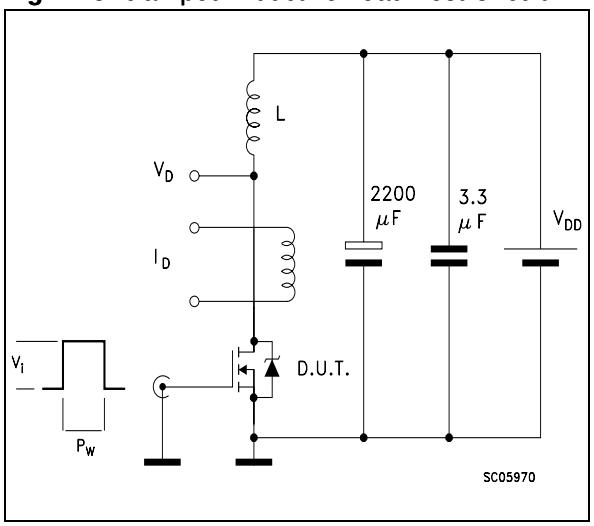


Fig. 2: Unclamped Inductive Waveform

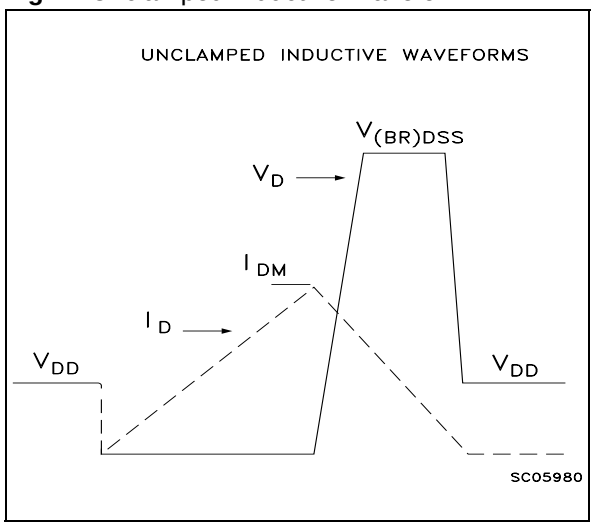


Fig. 3: Switching Times Test Circuits For Resistive Load

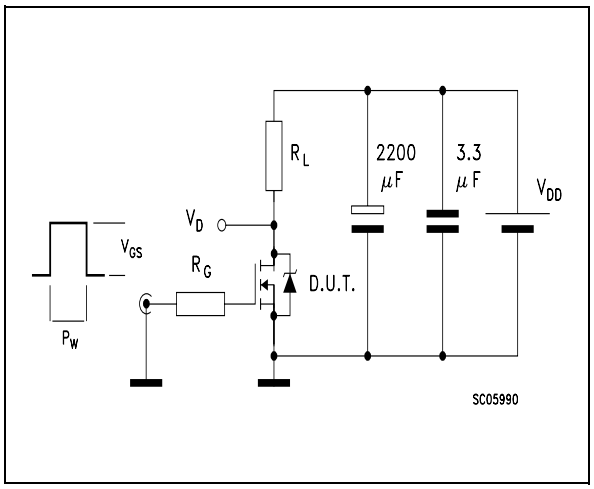


Fig. 4: Gate Charge test Circuit

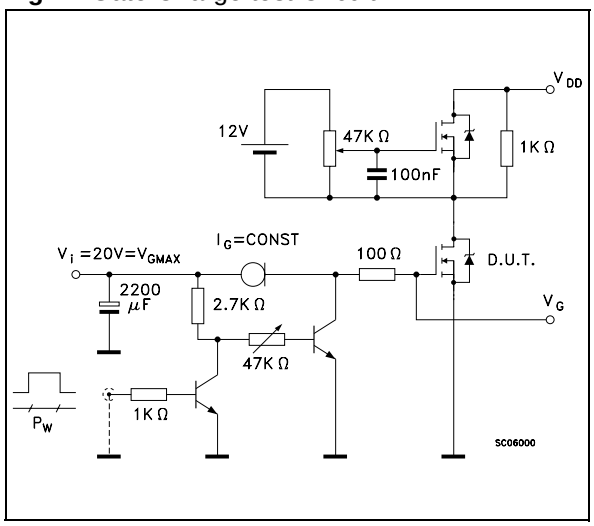
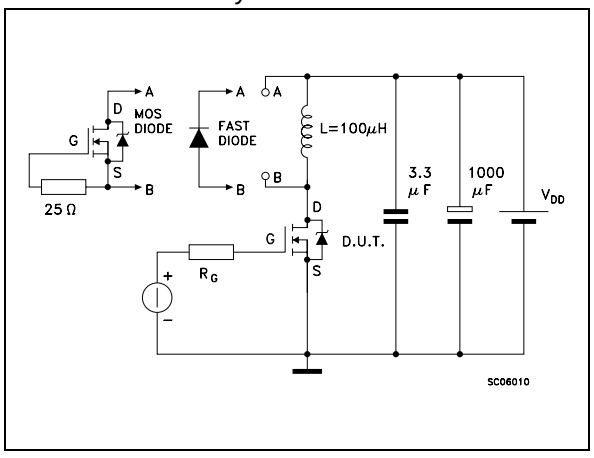
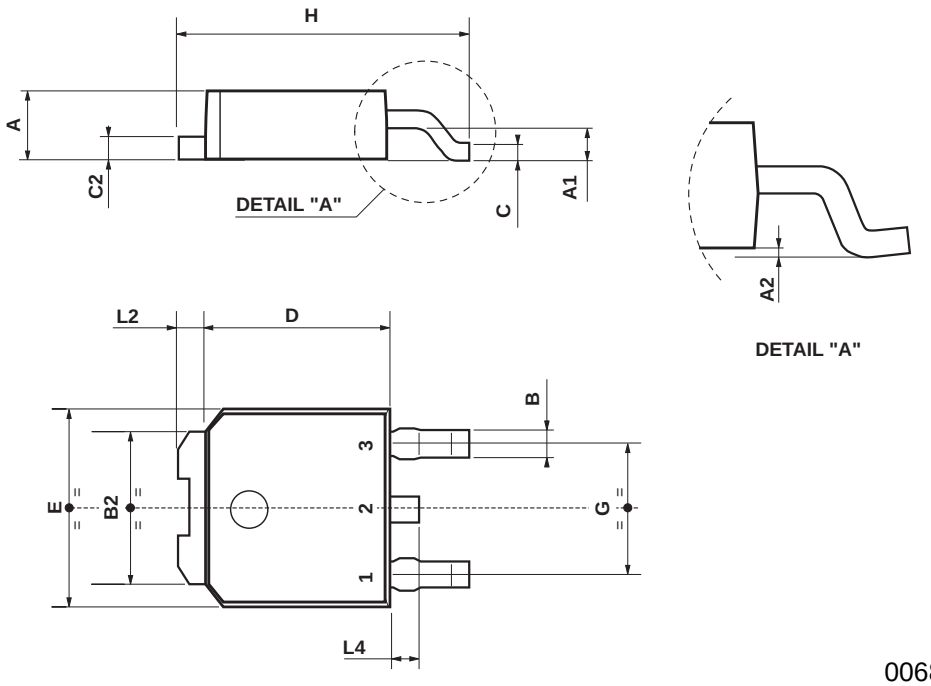


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



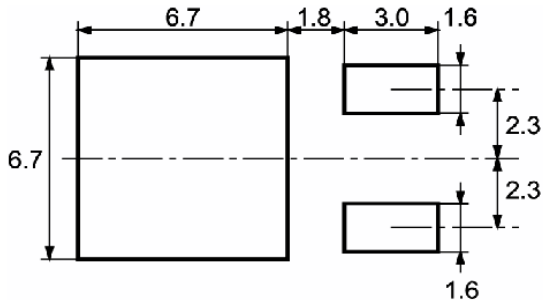
TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039



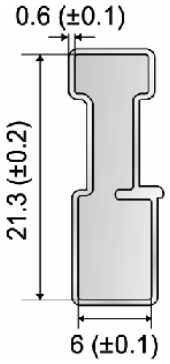
0068772-B

DPAK FOOTPRINT



All dimensions are in millimeters

TUBE SHIPMENT (no suffix)*



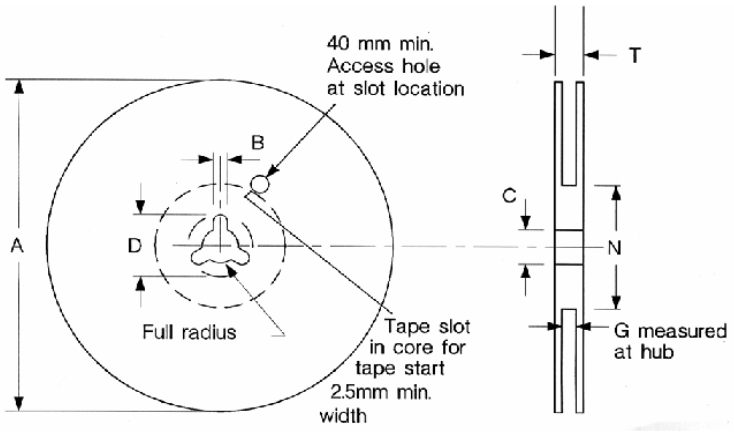
BASE QTY
75

BULK QTY
3000

Tube length 532 (±0.5)

All dimensions are in millimeters

TAPE AND REEL SHIPMENT (suffix "T4")*



REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641